

# SRAM

# 32K X 8 LOW POWER CMOS STATIC RAM

## FEATURES

- »VHigh speed access time: 12/15ns
- »VLow power supply current :
  - Operating : 90mA(max)
  - Standby : 10uA
- »VPower supply : +5V (± 10%)
- »VFully static operation – No clock or refreshing required
- »VAll inputs and outputs directly LVTTL compatible
- »VCommon I/O capability
- »VData retention voltage : 1.5V (min)
- »VAvailable packages :28-pin SOJ, SOP, TSOP-I (8x13.4mm forward type and reverse type).

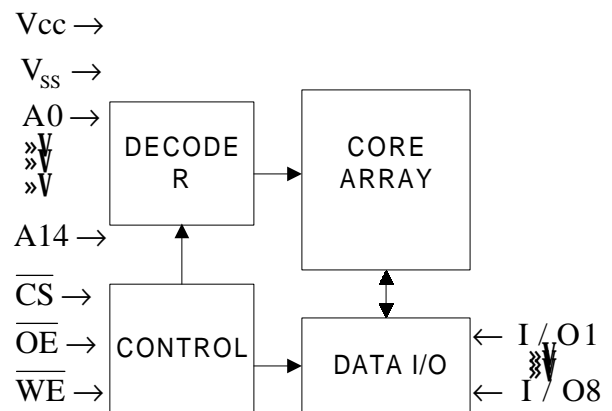
## PART NUMBER EXAMPLES

	PACKAGE	SPEED
T15M256C-12J	SOJ	12ns
T15M256C-12D	SOP	12ns
T15M256C-15P	TSOP-I(Forward)	15ns
T15M256C-15R	TSOP-I(Reverse)	15ns

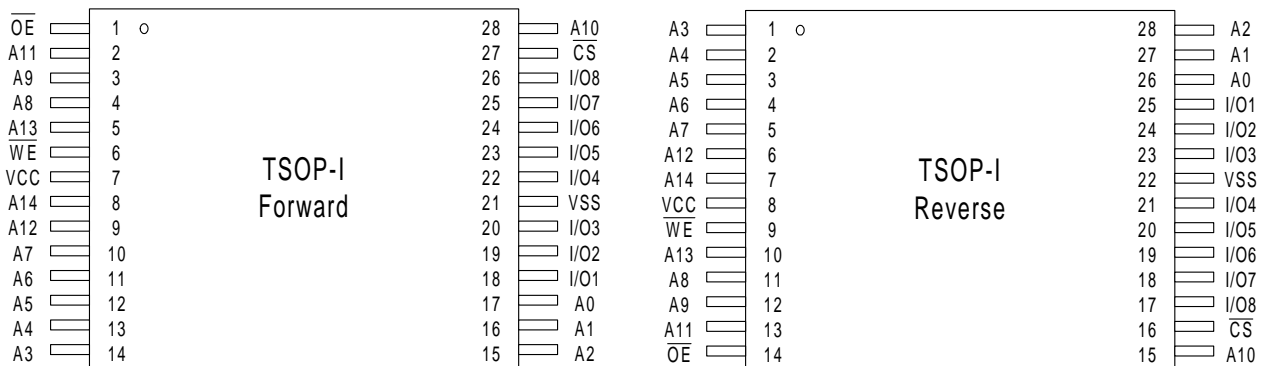
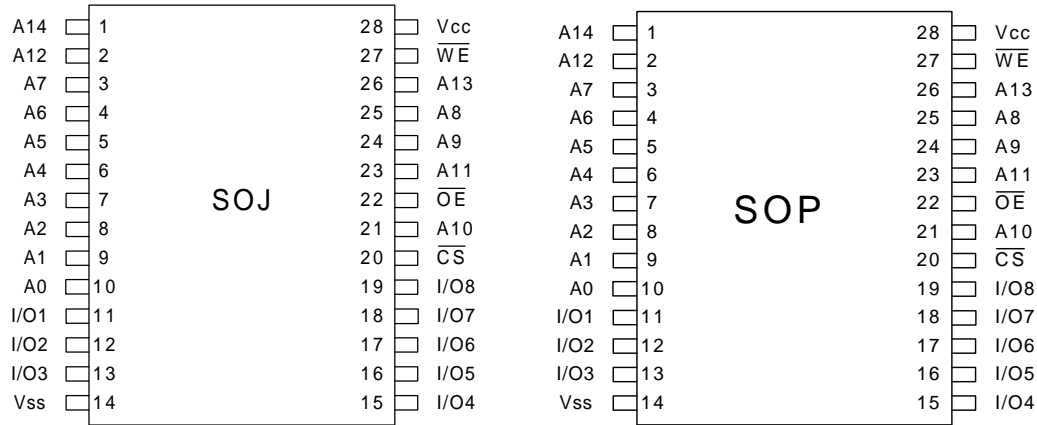
## GENERAL DESCRIPTION

The T15M256C is a low power CMOS static RAM. organized as 32,768 x 8 bits that operates on a single +5-volt power supply. Low operating and standby current . Data retention is guaranteed at a power supply voltage as low as 1.5V. This device is packaged in a standard 28-pin SOJ, SOP, TSOP-I forward and reverse type.

## BLOCK DIAGRAM



**PIN CONFIGURATION**



**PIN DESCRIPTION**

SYMBOL	DESCRIPTION
A0 - A14	Address Inputs
I/O1 - I/O8	Data Inputs/Outputs
$\overline{CS}$	Chip Select Inputs
$\overline{WE}$	Write Enable
$\overline{OE}$	Output Enable
Vcc	Power Supply
Vss	Ground

**DC CHARACTERISTICS ABSOLUTE MAXIMUM RATINGS**

PARAMETER	RATING	UNIT
Supply Voltage to Vss Potential	-0.5 to + 7V	V
Inputs to Vss Potential	-0.5 to Vcc +0.5	V
Power Dissipation	0.7	W
Storage Temperature	-60 to +150	°C

**RECOMMENDED OPERATING CONDITIONS**

PARAMETER	SYM	MIN	TYP	MAX	UNIT
Supply Voltage	Vcc	4.5	5	5.5	V
Input Voltage, low	V <sub>IL</sub>	-0.3	-	0.8	V
Input Voltage, high	V <sub>IH</sub>	2.2	-	Vcc+0.3	V
Ambient Temperature	T <sub>A</sub>	-40	-	85	°C

**TRUTH TABLE**

CS	OE	WE	MODE	I/O1- I/O8	Power
H	X	X	Not Selected	High-Z	Standby
L	H	H	Output Disable	High-Z	Active
L	L	H	Read	Data Out	Active
L	X	L	Write	Data In	Active

**OPERATING CHARACTERISTICS**

(Vcc = +5V / ± 10%, Vss = 0V, Ta = -40 to 85°C)

PARAMETER	SYM.	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Input Leakage Current	I <sub>LI</sub>	Vin=Vss to Vcc	-	-	1	μA	
Output Leakage Current	I <sub>LO</sub>	V <sub>I/O</sub> =Vss to Vcc, CS = V <sub>IH</sub> or OE= V <sub>IH</sub> or WE = V <sub>IL</sub>	-	-	1	μA	
Output Low Voltage	V <sub>OL</sub>	I <sub>OL</sub> = + 2.1mA	-	-	0.4	V	
Output High Voltage	V <sub>OH</sub>	I <sub>OH</sub> = - 1.0mA	2.4	-	-	V	
Operating Power Supply Current	I <sub>cc</sub>	CS = V <sub>IL</sub> , I/O=0mA Cycle = MIN. Duty = 100%	-12	-	-	90	mA
			-15	-	-	75	mA
Standby Power Supply Current	I <sub>SB</sub>	CS = V <sub>IH</sub> , Cycle=min, Duty=100%	-	-	0.3	mA	
	I <sub>SBI</sub>	CS ≥ V <sub>CC</sub> -0.2V	-	-	10	uA	

**CAPACITANCE**

(V<sub>CC</sub> = +5V / ± 10%, T<sub>a</sub> = 25°C, f = 1 MHz)

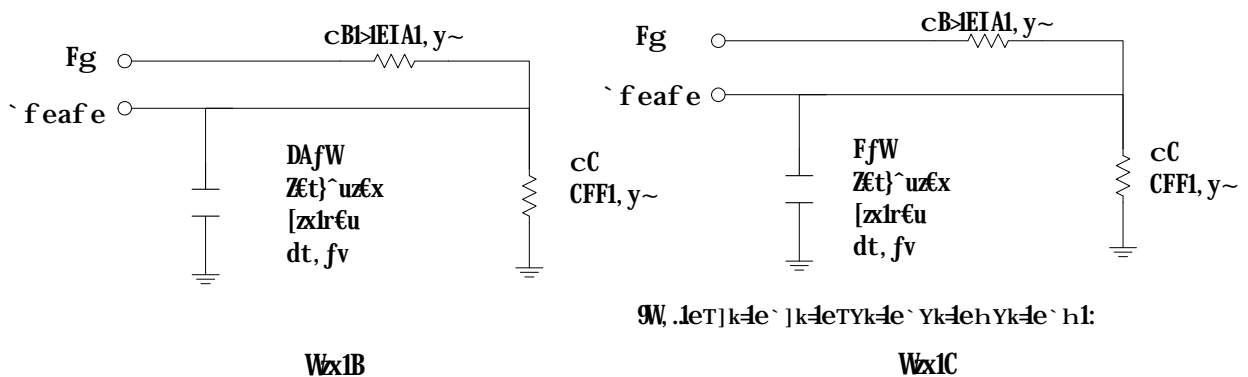
PARAMETER	SYMBOL	CONDITION	MAX.	UNIT
Input Capacitance	C <sub>IN</sub>	V <sub>IN</sub> = 0V	6	pF
Input/ Output Capacitance	C <sub>I/O</sub>	V <sub>OUT</sub> = 0V	8	pF

**Note:** These parameters are sampled but not 100% tested.

**AC TEST CONDITIONS**

PARAMETER	CONDITIONS
Input Pulse Levels	0V to 3V
Input Rise and Fall Times	3 ns
Input and Output Timing Reference Level	1.5V
Output Load	See Fig. 1,2

**AC TEST LOADS AND WAVEFORM**



**AC CHARACTERISTICS**

 ( $V_{cc} = +5V / \pm 10\%$ ,  $V_{ss} = 0V$ ,  $T_a = -40$  to  $85^\circ C$ )

**(1) READ CYCLE**

PARAMETER	SYM.	-12ns		-15ns		UNIT
		MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	tRC	12	1/2	15	1/2	ns
Address Access Time	tAA	1/2	12	1/2	15	ns
Chip Select Access Time	tACS	1/2	12	1/2	15	ns
Output Enable to Output Valid	tAOE	1/2	7	1/2	7	ns
Chip Selection to Output in Low Z	tCLZ*	3	1/2	3	1/2	ns
Output Enable to Output in Low Z	tOLZ*	0	1/2	0	1/2	ns
Chip Deselection to Output in High Z	tCHZ*	0	6	0	7	ns
Output Disable to Output in High Z	tOHZ*	0	6	0	7	ns
Output Hold from Address Change	tOH	3	1/2	3	1/2	ns

\* These parameters is measured with 30pF test load.

**(2) WRITE CYCLE**

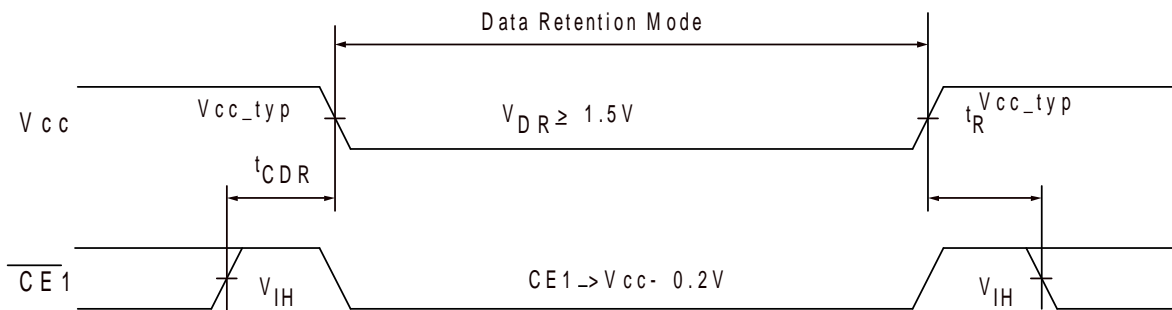
PARAMETER	SYM.	-12ns		-15ns		UNIT
		MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	tWC	12	1/2	15	1/2	ns
Chip Selection to End of Write	tCW	10	1/2	11	1/2	ns
Address Valid to End of Write	tAW	10	1/2	11	1/2	ns
Address Setup Time	tAS	0	1/2	0	1/2	ns
Write Pulse Width	tWP	10	1/2	11	1/2	ns
Write Recovery Time	tWR	0	1/2	0	1/2	ns
Data Valid to End of Write	tDW	8	1/2	8	1/2	ns
Data Hold from End of Write	tDH	0	1/2	0	1/2	ns
Write to Output in High Z	tWHZ*	1/2	6	1/2	6	ns
Output Active from End of Write	tOW	0	1/2	0	1/2	ns

\* These parameters is measured with 30pF test load.

**DATA RETENTION CHARACTERISTICS**

Item	Symbol	Test Condition	Min	Typ	max	unit
Vcc for data retention	V <sub>DR</sub>	$\overline{CS} \geq V_{cc} - 0.2V$	1.5	-	-	V
Data retention current	I <sub>DR</sub>	$V_{cc} = 3.0, \overline{CS} \geq V_{cc} - 0.2V$	-		10	uA
Data retention set-up time	t <sub>CDR</sub>	See data retention waveform	0	-	-	ms
Recovery time	t <sub>R</sub>		5	-	-	

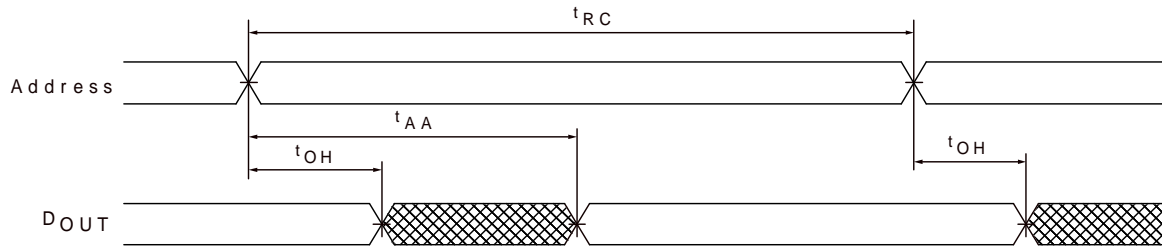
**DATA RETENTION WAVE FORM**



**TIMING WAVEFORMS**

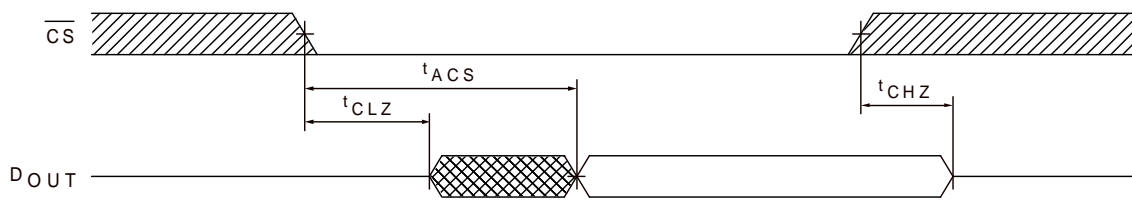
**READ CYCLE 1**

(Address Controlled)



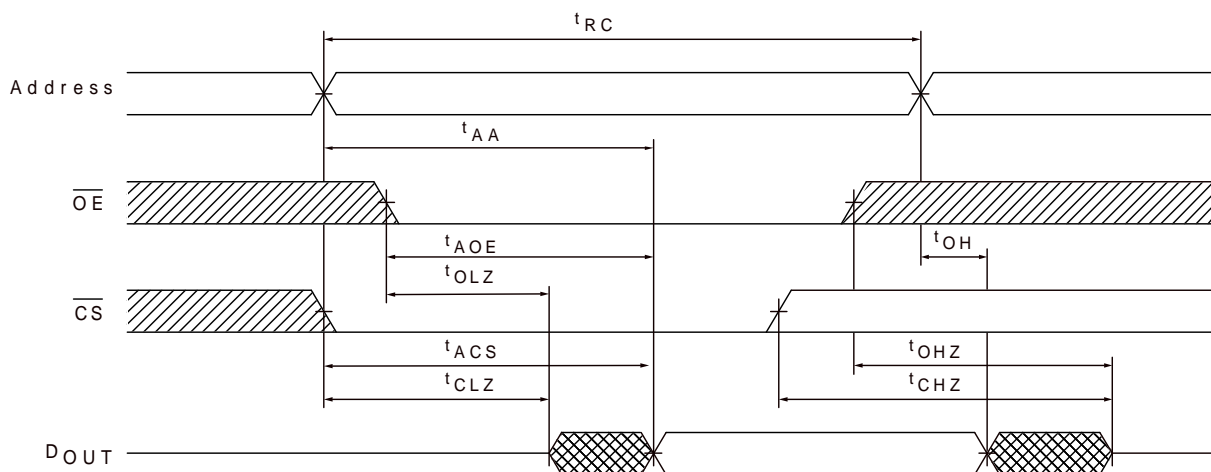
**READ CYCLE 2**



(Chip Select Controlled)



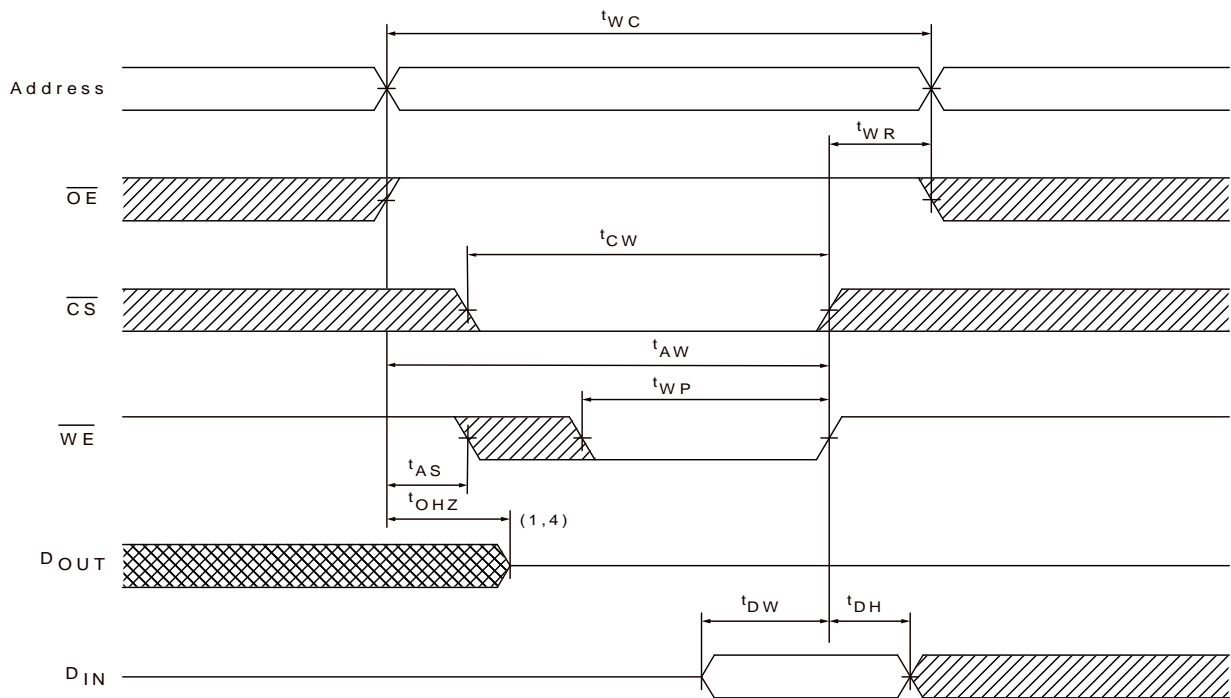
**READ CYCLE 3**

(Output Enable Controlled)

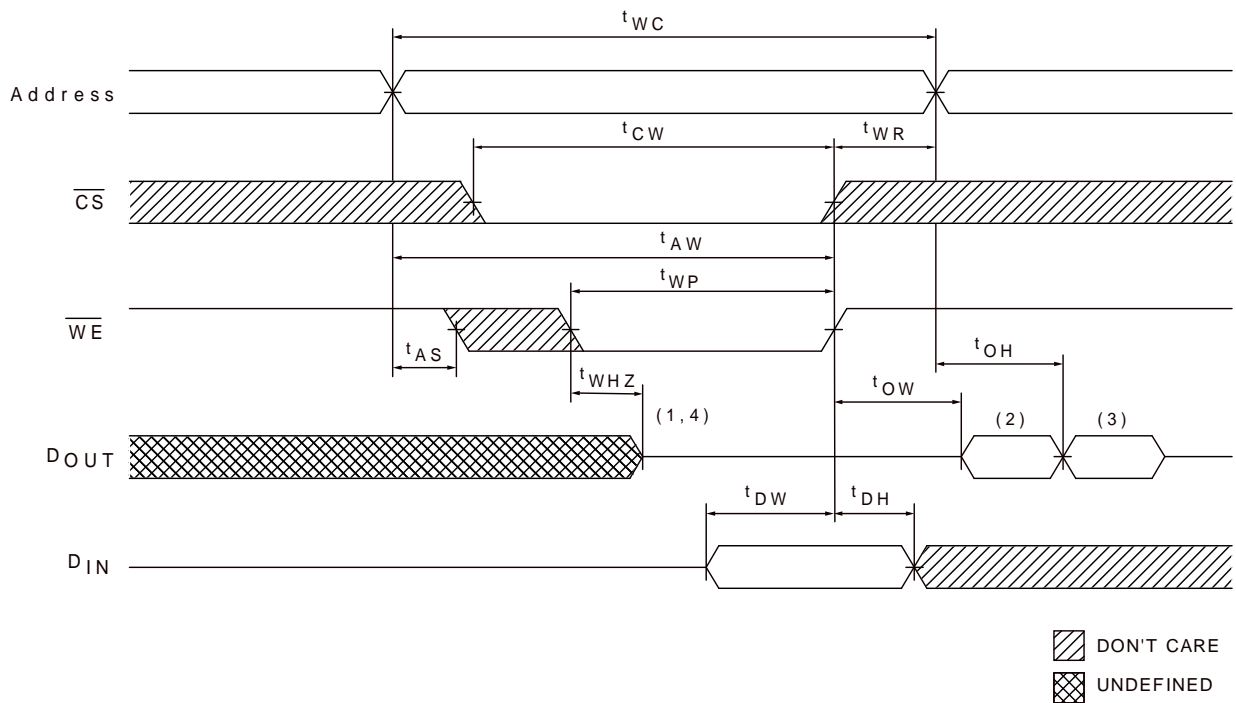


 DON'T CARE  
 UNDEFINED

**WRITE CYCLE 1 ( $\overline{OE}$  CLOCK)**



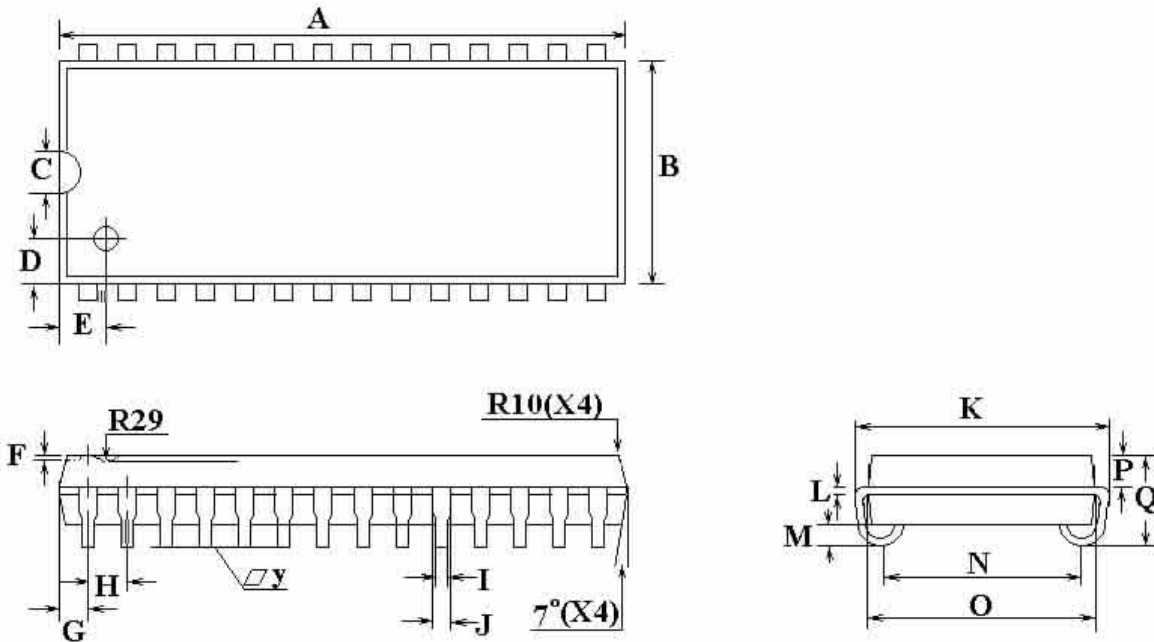
**WRITE CYCLE 2 ( $\overline{OE} = V_{IL}$  Fixed)**





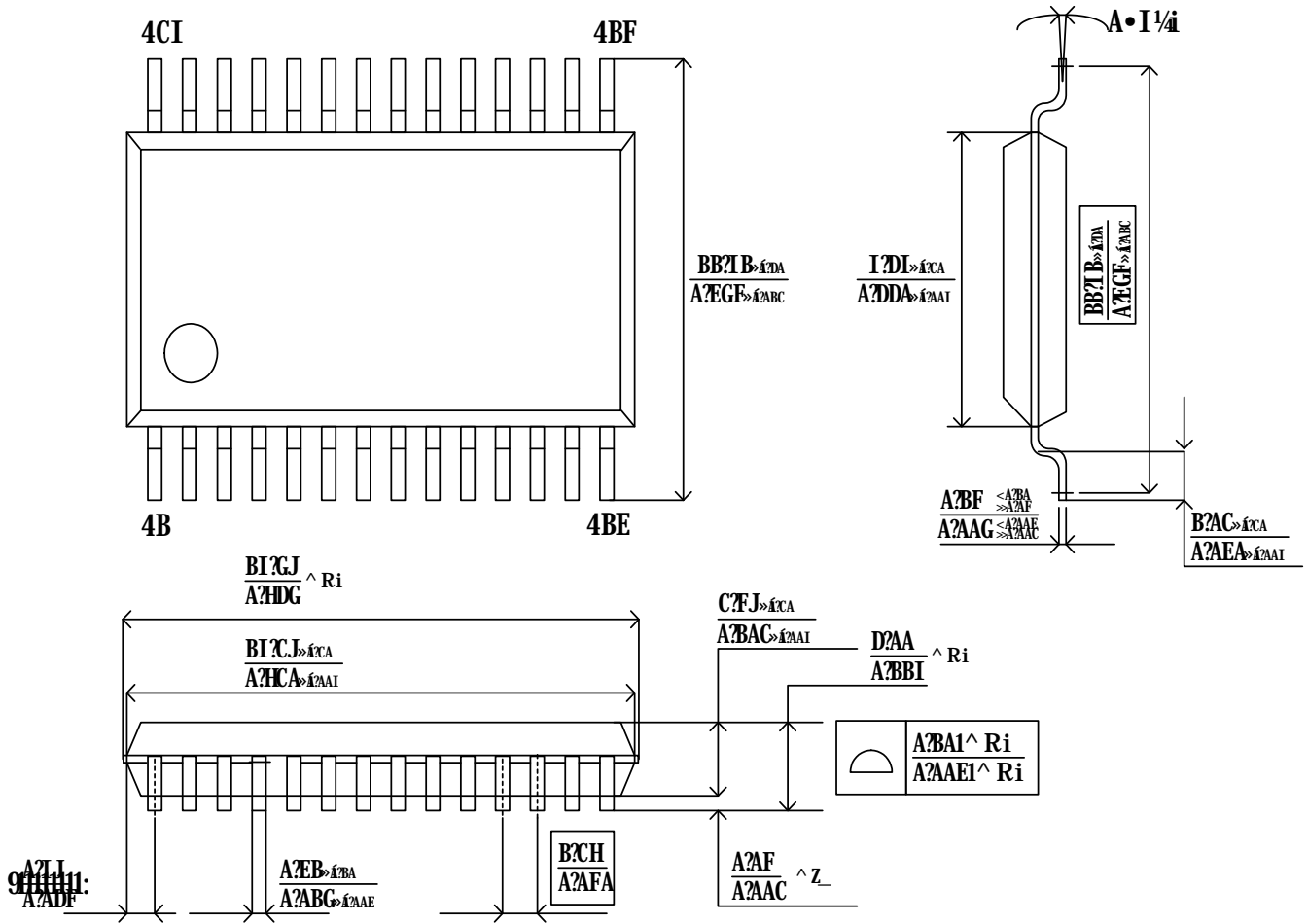
- Notes:
1. During this period, I/O pins are in the output state, so input signals of opposite phase to the outputs should not be applied.
  2. The data output from  $D_{OUT}$  are the same as the data written to  $D_{IN}$  during the write cycle.
  3.  $D_{OUT}$  provides the read data for the next address.
  4. Transition is measured  $\pm 500$  mV from steady state with  $C_L = 5\text{pF}$ . This parameter is guaranteed but not 100% tested.
  5. If  $\overline{OE}$  is low during a  $\overline{WE}$  controlled write cycle, the write pulse width must be the larger of  $t_{WP}$  or  $(t_{WHZ} + t_{DW})$  to allow the I/O drivers to turn off and data to be placed on the bus for the required  $t_{DW}$ . If  $\overline{OE}$  is high during a  $\overline{WE}$  controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified  $t_{WP}$ .

**PACKAGE DIMENSIONS**  
**28-LEAD SOJ SRAM (300 mil)**



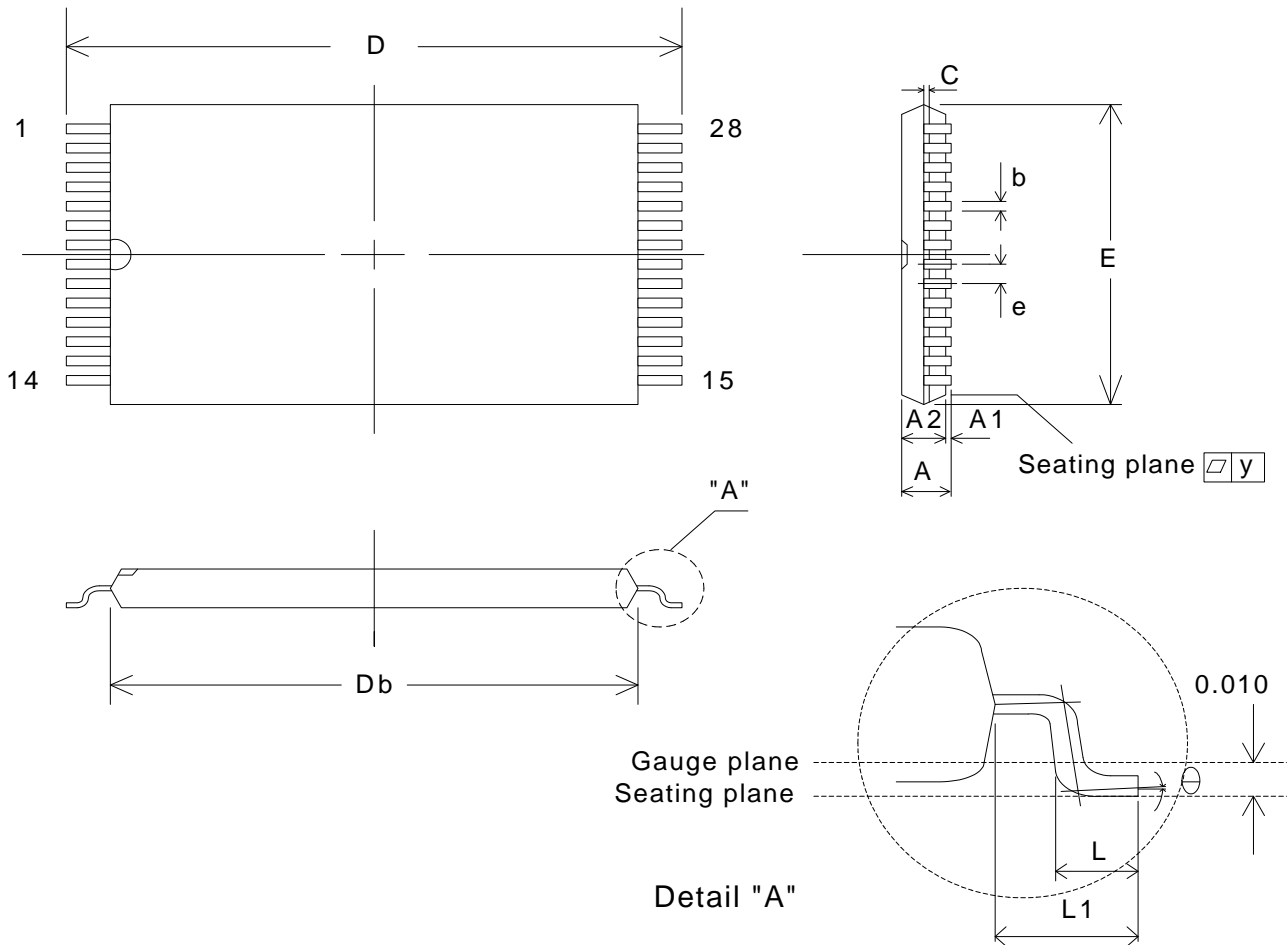
SYMBOL	DIMENSIONS IN INCHES	DIMENSIONS IN MM
A	0.710±0.002	18.03±0.05
B	0.336±0.003	8.53±0.08
C	0.060±0.002	1.52±0.05
D	0.050±0.001	1.27±0.03
E	0.063±0.001	1.63±0.03
F	0.015±0.002	0.38±0.05
G	0.030±0.002	0.76±0.05
H	0.050±0.002	1.27±0.05
I	0.018±0.002	0.46±0.05
J	0.028±0.002	0.71±0.05
K	0.337±0.002	8.56±0.05
L	0.010±0.001	0.25±0.03
M	0.026±0.002	0.66±0.05
N	0.268±0.003	6.81±0.08
O	0.300±0.002	7.62±0.05
P	0.053±0.001	1.35±0.03
Q	0.140±0.004	3.56±0.10
y	0.004(MAX)	0.10(MAX)

**PACKAGE DIMENSIONS**  
**28-LEAD SOP**



**PACKAGE DIMENSIONS**

**28-LEAD TSOP-I FORWARD AND REVERSE (8X13.4mm)**



SYMBOL	DIMENSIONS IN INCHES	DIMENSIONS IN MM
A	0.047(max.)	1.20(max.)
A1	0.004»í0.002	0.10»í0.05
A2	0.039»í0.002	1.00»í0.05
b	0.008(typ.)	0.20(typ.)
c	0.006(typ.)	0.15(typ.)
Db	0.465»í0.004	11.80»í0.10
E	0.315»í0.004	8.00»í0.10
e	0.022(typ.)	0.55(typ.)
D	0.528»í0.008	13.40»í0.20
L	0.020»í0.004	0.50»í0.10
L1	0.0315»í0.004	0.80»í0.10
y	0.004(max.)	0.10(max.)
½	0¼ ~ 5¼	0¼ ~ 5¼